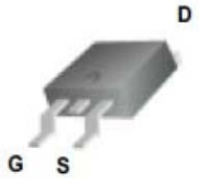
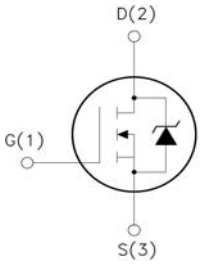
CTKD80N04

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 50nC (Typ.).
- ☐ BVDSS=40V,I_D=80A
- ☐ R_{DS}(on) : 6.5mΩ (Max) @V_G=10V
- ☐ 100% Avalanche Tested

TO-252





1.Gate (G)
2.Drain (D)
3.Source (S)

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	56	A
Pulsed Drain Current	I_{DM}	350	A
Maximum Power Dissipation	P_D	90	W
Derating factor		0.6	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	670	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	1.67	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	40	45	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	5.3	6.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=20V,V_{GS}=0V, F=1.0MHz	-	3215	-	PF
Output Capacitance	C_{oss}		-	750	-	PF
Reverse Transfer Capacitance	C_{rss}		-	390	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=20V, R_L=1Ω V_{GS}=10V,R_G=3Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	11	-	nS
Total Gate Charge	Q_g	V_{DS}=20V,I_D=20A, V_{GS}=10V	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 20A di/dt = 100A/μs(Note3)	-	33	-	nS
Reverse Recovery Charge	Qrr		-	34	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : Tj=25℃,V_{DD}=20V,V_G=10V,L=1mH,Rg=25Ω，I_{AS}=36A

Typical Electrical and Thermal Characteristics (Curves)

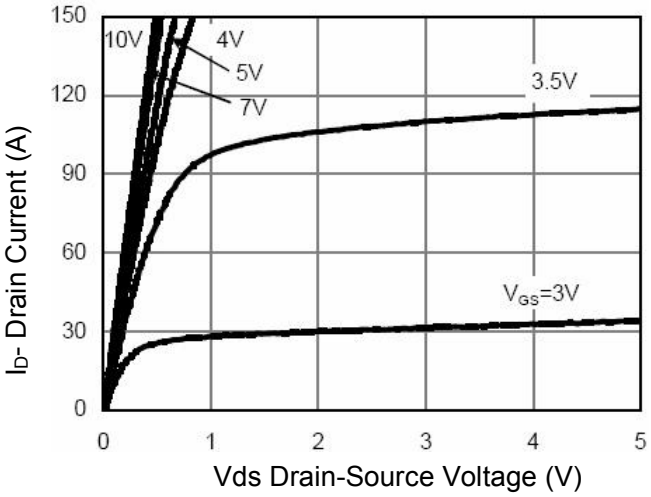


Figure 1 Output Characteristics

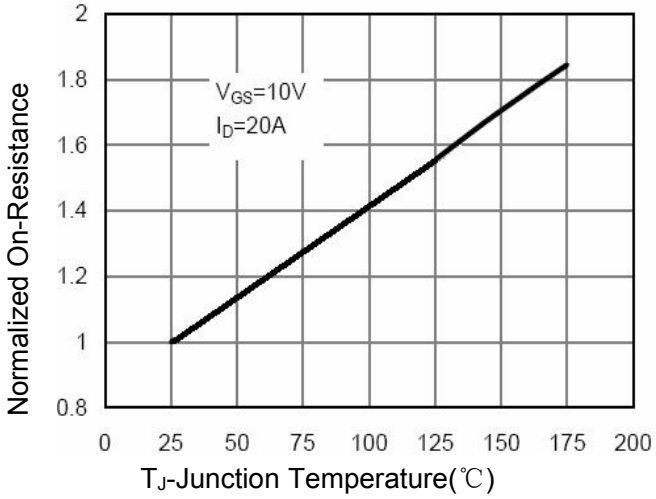


Figure 4 Rdson-JunctionTemperature

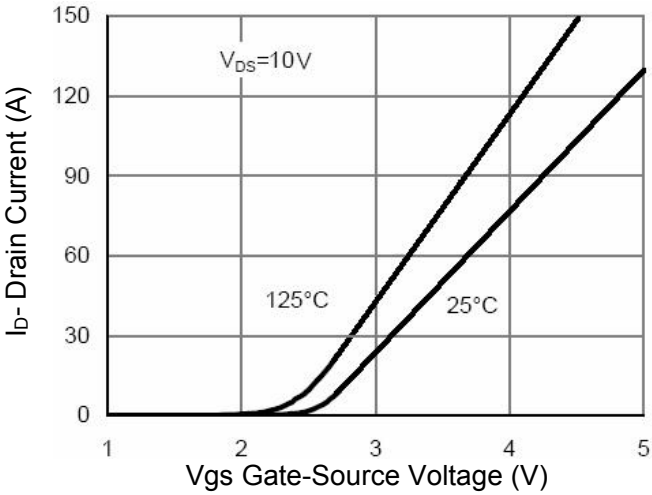


Figure 2 Transfer Characteristics

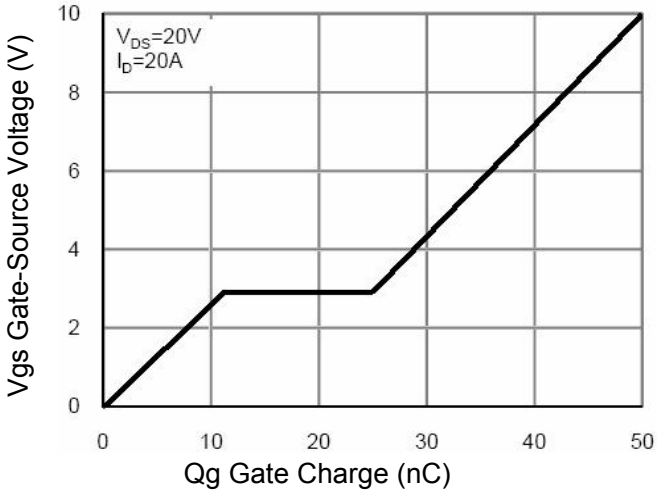


Figure 5 Gate Charge

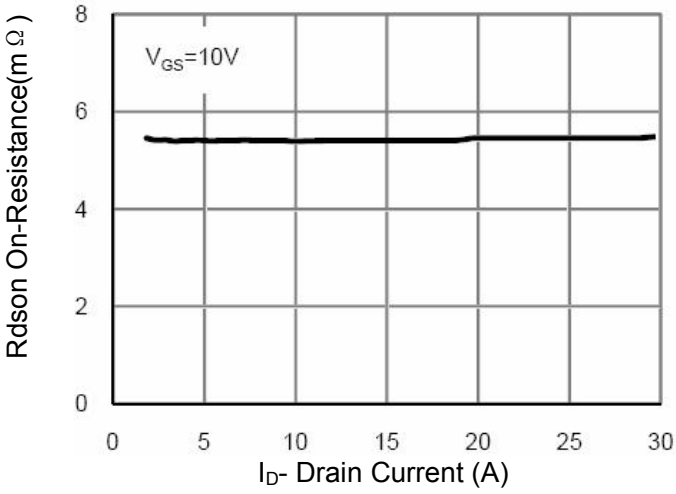


Figure 3 Rdson- Drain Current

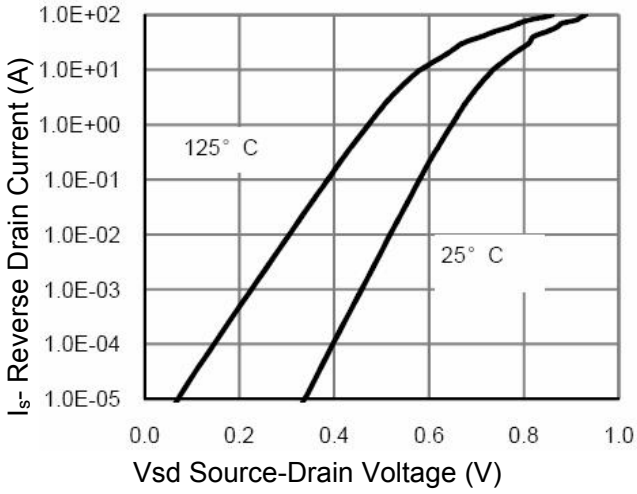


Figure 6 Source- Drain Diode Forward

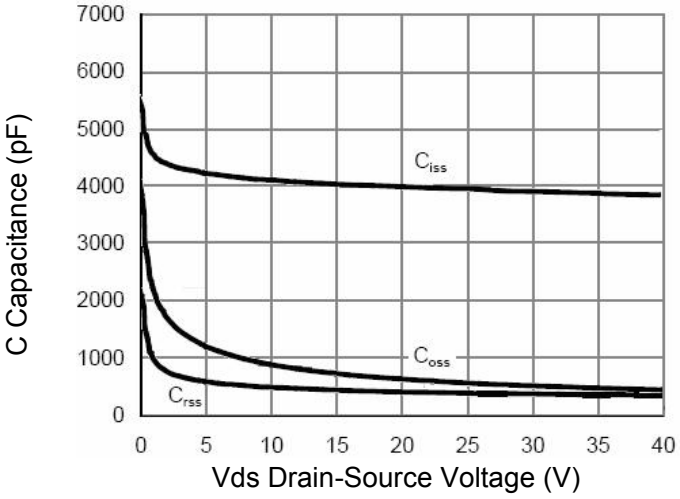


Figure 7 Capacitance vs Vds

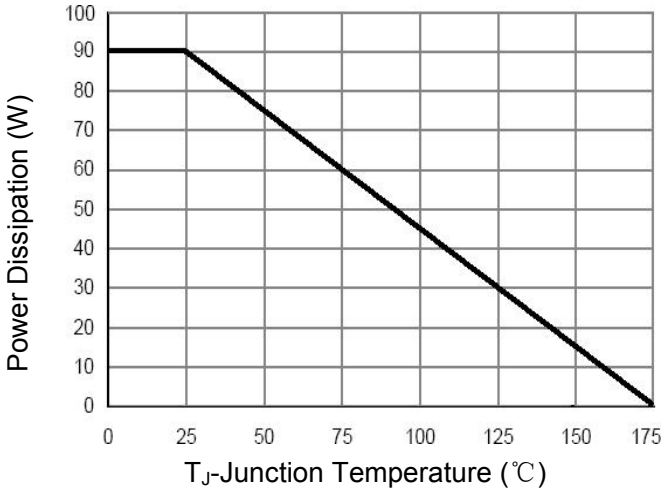


Figure 9 Power De-rating

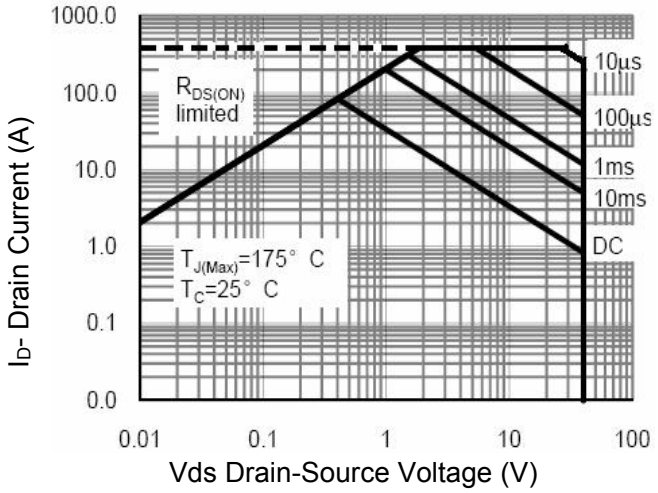


Figure 8 Safe Operation Area

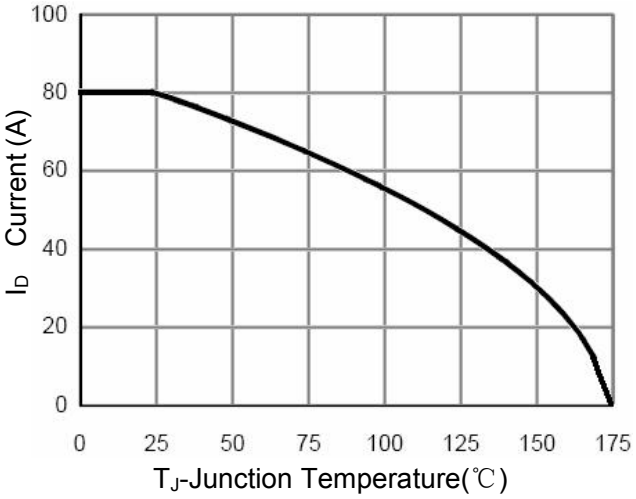


Figure 10ID Current- Junction Temperature

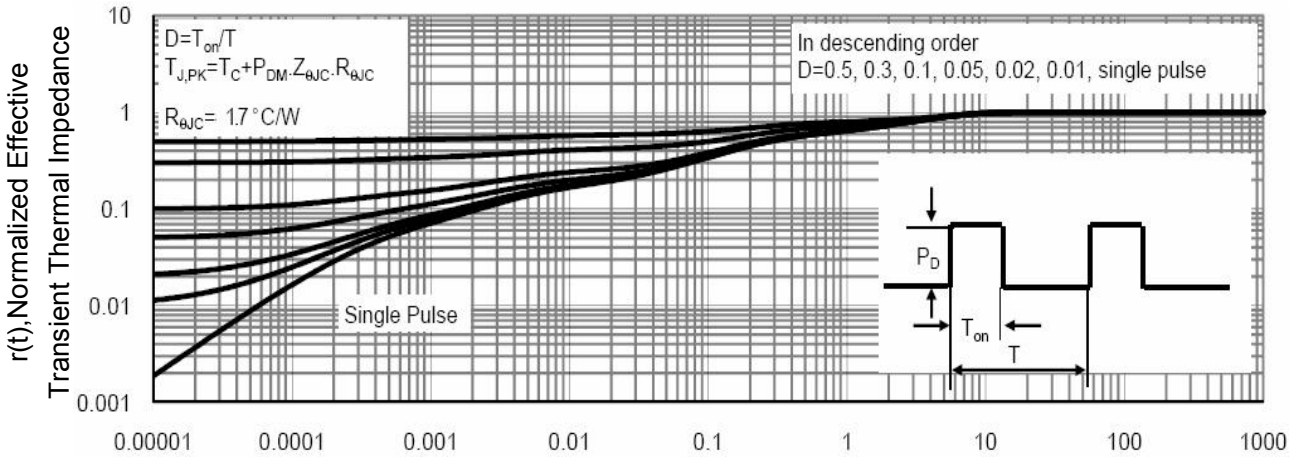
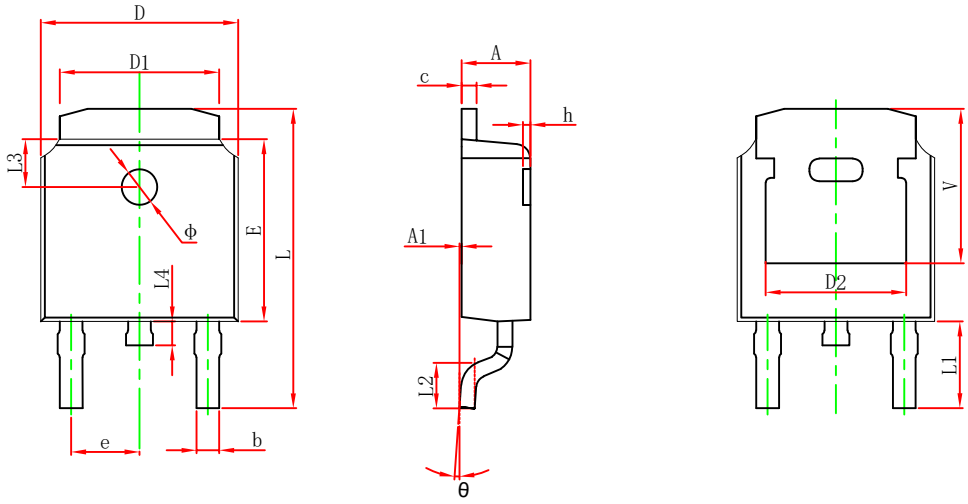


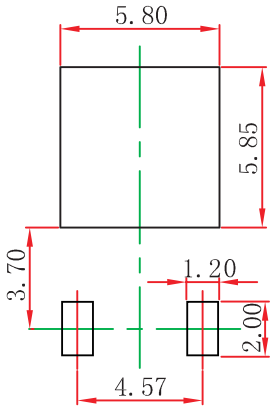
Figure 11 Normalized Maximum Transient Thermal Impedance

Package Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.700	0.860	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.300	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggest Pad Layout



NOTE:

1. Controlling dimension: in millimeters.
2. General tolerance: ±0.05mm.
3. The pad layout is for reference purposes only.